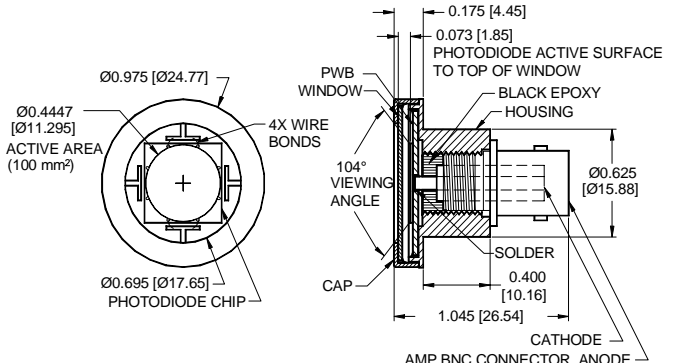


### PACKAGE DIMENSIONS inch (mm)



### BNC CONNECTOR PACKAGE

ACTIVE AREA = .4447 (11.295) DIA = 100 mm<sup>2</sup>

### FEATURES

- Blue enhanced
- Photoconductive
- High speed
- Low dark current

### DESCRIPTION

Large area, instrumentation grade, blue enhanced silicon photodiode. Designed for low capacitance high speed photoconductive applications. Packaged in a BNC connector package.

### APPLICATIONS

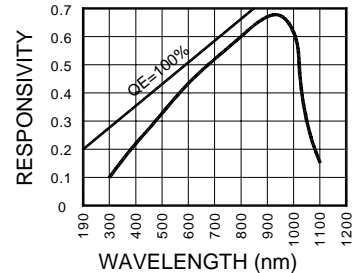
- Instrumentation
- Power meters
- Colorimeters
- Laser power meters

### ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
VBR	Reverse Voltage		100	V
TS	Storage Temperature	-20	+70	°C
TO	Operating Temperature Range	-10	+60	°C
TS	Soldering Temperature*	N/A	N/A	°C
I <sub>max</sub>	Light Current		0.5	mA

\*1/16 inch from case for 3 secs max

### SPECTRAL RESPONSE



### ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
ISC	Short Circuit Current	H = 100 fc, 2850 K	1.0	1.3		mA
ID	Dark Current	H = 0, VR = 10V		10	30	nA
RSH	Shunt Resistance	H = 0, VR = 10 mV	15	30		MΩ
TC RSH	RSH Temp. Coefficient	H = 0, VR = 10 mV		-8		% / °C
CJ	Junction Capacitance	H = 0, VR = 10V**		300		pF
I <sub>range</sub>	Spectral Application Range	Spot Scan	350		1100	nm
I <sub>p</sub>	Spectral Response - Peak	Spot Scan		950		nm
VBR	Breakdown Voltage	I = 10 μA	30	50		V
NEP	Noise Equivalent Power	VR = 10 @ Peak		3x10 <sup>-13</sup>		W/ √Hz
tr	Response Time	RL = 1 KΩ VR = 50V		25		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. \*\*f = 1 MHz